

Taiwan Semiconductor

N-Channel Power MOSFET

FEATURES

- Latest super-junction technology
- Low gate charge capacitance
- High gate noise immunity
- RoHS compliant
- Halogen-free

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- Switching applications
- HV motor driver
- Industrial

KEY PERFORMANCE PARAMETERS					
PARAMETER	VALUE	UNIT			
V _{DS} @ T _{j,max}	650	V			
R _{DS(on)} (max)	69	mΩ			
$Q_{g,typ}$	89	nC			

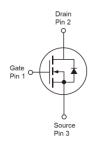












ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	600	V			
Gate-Source Voltage		V _G s	±30	V		
Continuous Drain Current	T _C = 25°C	I _D	24	Α		
Pulsed Drain Current (Note 1)	I _{DM}	96	А			
Total Power Dissipation @ T _C = 2	P _D	89	W			
Single Pulse Avalanche Energy (Eas	840	mJ			
Single Pulse Avalanche Current	I _{AS}	5.8	Α			
Operating Junction and Storage	T _J , T _{STG}	- 55 to +150	°C			

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	Rejc	1.4	°C/W		
Junction to Ambient Thermal Resistance (Note 3)	R _{ΘJA}	65	°C/W		

Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 50mH, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$.
- 3. Reja is the sum of the junction-to-case and case-to-ambient thermal resistances. Reja is guaranteed by design while Reja is determined by the user's board design.

1



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 1mA$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 3.5 \text{mA}$	V _{GS(TH)}	4	4.8	6	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	Igss			±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V	I _{DSS}			100	μA
David On the One Other Business	V _{GS} = 12V, I _D = 8A	Б		50	60	mΩ
Drain-Source On-State Resistance	V _G S = 10V, I _D = 8A	R _{DS(on)}		52	69	
Dynamic (Note 5)						
Total Gate Charge		Qg		89		nC
Gate-Source Charge	$V_{DS} = 480V, I_{D} = 24A,$ $V_{GS} = 10V$	Qgs		23		
Gate-Drain Charge	VGS = 10V	Q _{gd}		50		
Input Capacitance		C _{iss}		3551		
Output Capacitance	$V_{DS} = 300V, V_{GS} = 0V,$ f = 100kHz	Coss		96		pF
Reverse Transfer Capacitance		Crss		12		
Gate Resistance	f = 1.0MHz	Rg		1		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		37		
Turn-On Rise Time	$V_{DD} = 300V, R_G = 3.3\Omega,$	t _r		59		
Turn-Off Delay Time	I _D = 24A, V _{GS} = 10V	t _{d(off)}		74		ns ns
Turn-Off Fall Time		t _f		4.4		
Source-Drain Diode						•
Forward Voltage (Note 4)	Is = 8A, VGS = 0V	V _{SD}		0.8	1.5	V
Reverse Recovery Time	I _S = 12A	t _{rr}		349		ns
Reverse Recovery Charge	dl _F /dt = 100A/µs	Qrr		6.1		μC

Notes:

- 4. Pulse test: Pulse Width $\leq 300 \mu s$, duty cycle $\leq 2\%$.
- Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

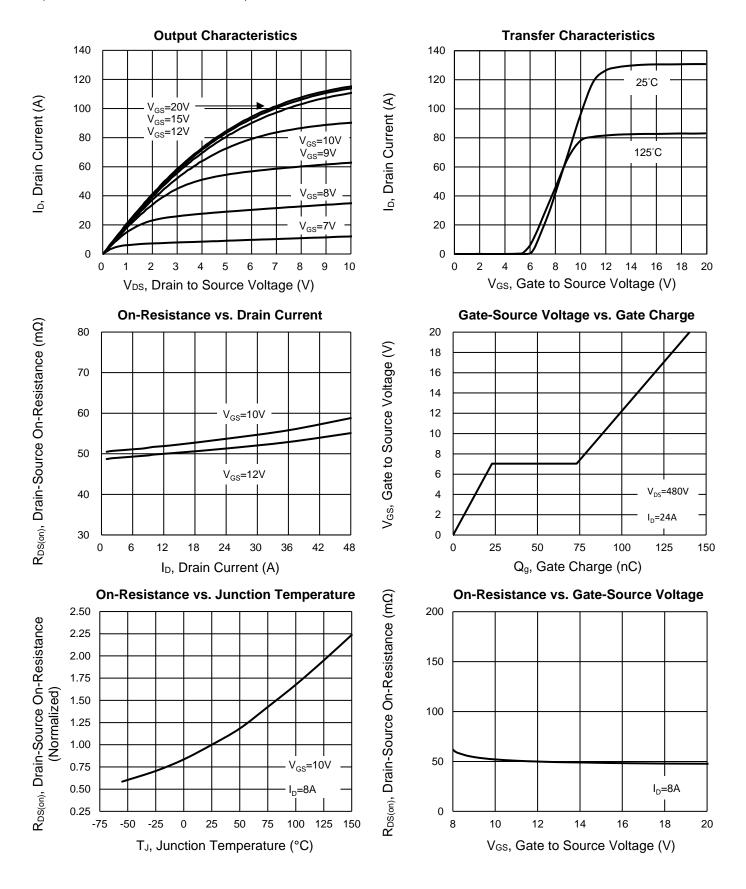
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM60NE069CIT COG	ITO-220TL	50pcs / Tube



CHARACTERISTICS CURVES

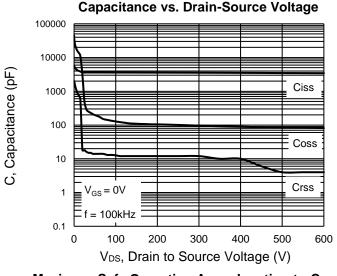
(T_C = 25°C unless otherwise noted)

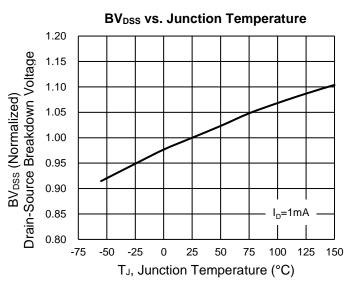




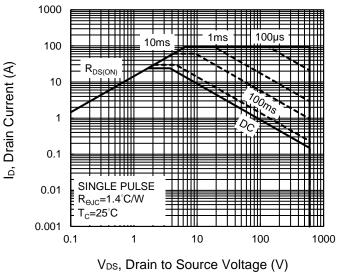
CHARACTERISTICS CURVES

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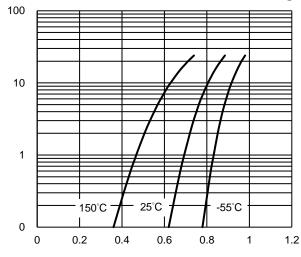




Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

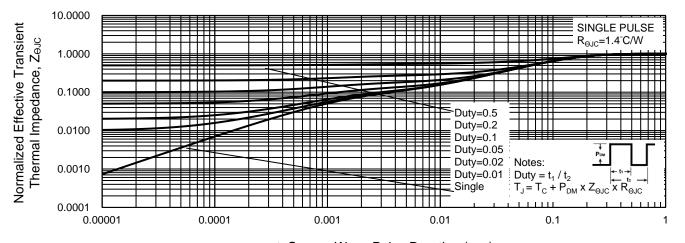


e Voltage (V) V_{SD}, Body Diode Forward Voltage (V)

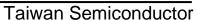


Reverse Drain Current (A)

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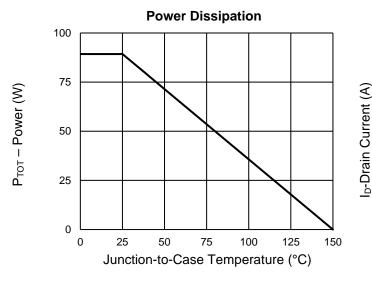
t, Square Wave Pulse Duration (sec)

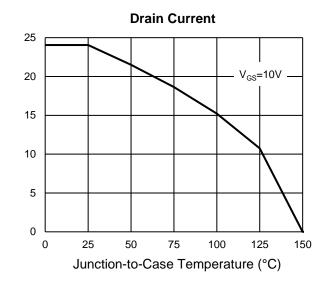




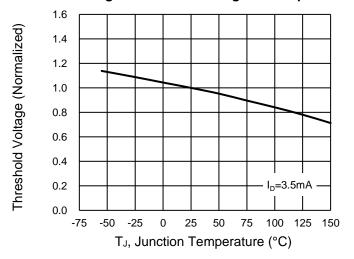
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$





Normalized gate threshold voltage vs Temperature



Version: B2407

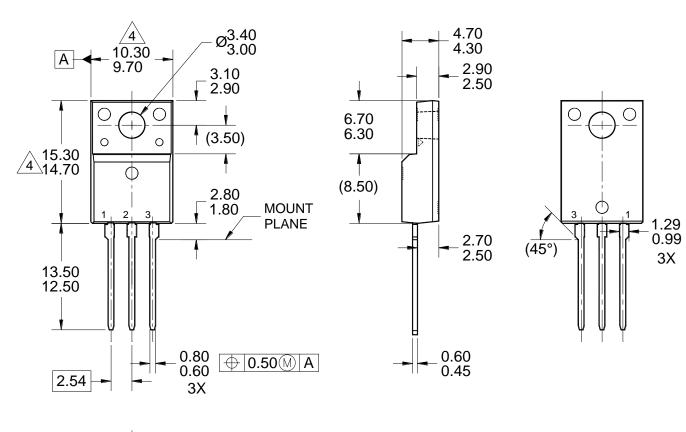
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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

ITO-220TL





NOTES: UNLESS OTHERWISE SPECIFIED

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PACKAGE OUTLINE REFERENCE: EIAJ ED-7500A-1, SC-91.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
 - 5. DWG NO. REF: HQ2SD07-ITO220TL-016 REV B.



MARKING DIAGRAM

Y = YEAR CODE WW = WEEK CODE (01~52) L = LOT CODE (1~9, A~Z) F = FACTORY CODE



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